

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions and listings of claims in the application:

1-12 (Canceled).

13. (Currently Amended) A plasma processing apparatus that performs plasma processing on a ~~workpiece~~ semiconductor wafer placed on an electrode provided inside a processing chamber, comprising:

an electrically conductive ring body encompassing the periphery of said ~~workpiece~~ semiconductor wafer placed on said electrode;

an electrically insulating ring body encompassing the periphery of said electrically conductive ring body;

a thermal conductivity adjusting member, for adjusting a thermal conductivity between the electrode and the electrically conductive ring body, provided between said electrode and said electrically conductive ring body, attached to ~~a whole area of a bottom surface of~~ said electrically conductive ring body, made of aluminum, and forming an Al₂O₃ film at a surface of the thermal conductivity adjusting member; and

a means for pressure application for applying a pressure through the thermal conductive adjusting member to raise the thermal conductivity between said electrode and said electrically conductive ring body and is capable of adjusting the level of the pressure,

wherein the means for pressure application is not exposed to the space of performing said plasma processing.

14. (Previously Presented) A plasma processing apparatus according to claim 13, further comprising a means for heat application provided at said electrically insulating ring body.

15. (Currently Amended) A plasma processing apparatus according to claim 13, wherein said thermal conductivity between said ~~workpiece~~ semiconductor wafer and said electrode is represented as Q,

wherein an area of a surface of said electrically conductive ring body contacting said plasma is represented as S1,

wherein an area of a surface of said electrically conductive ring body contacting said electrode is represented as S2, and

wherein said thermal conductivity adjusting member achieves a thermal conductivity R express as $R = Q \times S1/S2$.

16. (Canceled).

17. (Currently Amended) A plasma processing apparatus according to claim 13, further comprising a gas supply passage means through which a heat transfer gas is supplied to a space between said ~~workpiece~~ semiconductor wafer and said electrode.

18. (Currently Amended) A plasma processing apparatus according to claim 13, wherein the means for pressure application sets the temperature at said electrically conductive ring body and the temperature at said ~~workpiece~~ semiconductor wafer roughly equal to each other.